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on October 9, 2006.

TOWNSEND and TOWNSEND and CREW LLP

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PATENT  
Attorney Docket No.: A8067/T51700  
AMAT No.:  
008067/DSM/HDP/CVD/JPFEIFER  
TTC No.: 016301-051700US

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re application of:

Hemant P. Mungekar et al.

Application No.: 10/660,813

Filed: September 12, 2003

For: REACTIVE ION ETCHING FOR  
SEMICONDUCTOR DEVICE  
FEATURE TOPOGRAPHY  
MODIFICATION

Customer No.: 57385

Confirmation No. 7055

Examiner: McDonald, Rodney Glenn

Technology Center/Art Unit: 1753

AMENDMENT

Mail Stop Amendment  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

In response to the Office Action mailed July 19, 2006, please enter the following  
amendments and remarks:

**A Listing of Claims** begins on page 2 of this paper.

**Remarks** begin on page 7 of this paper.